# Old Company Name in Catalogs and Other Documents

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April 1<sup>st</sup>, 2010 Renesas Electronics Corporation

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# MOS FIELD EFFECT TRANSISTOR



2SK2479

# SWITCHING N-CHANNEL POWER MOS FET INDUSTRIAL USE

#### **DESCRIPTION**

The 2SK2479 is N-Channel MOS Field Effect Transistor designed for high voltage switching applications.

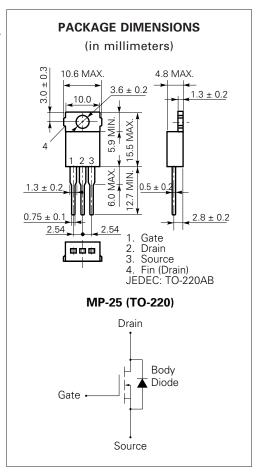
#### **FEATURES**

- Low On-Resistance  $R_{DS(on)} = 7.5 \ \Omega \ (V_{GS} = 10 \ V, \ I_{D} = 2.0 \ A)$
- Low Ciss Ciss = 485 pF TYP.
- High Avalanche Capability Ratings

### ABSOLUTE MAXIMUM RATINGS (TA = 25 °C)

Drain to Source Voltage	Voss	900	V
Gate to Source Voltage	Vgss	±30	V
Drain Current (DC)	ID(DC)	±3.0	Α
Drain Current (pulse)*	D(pulse)	±8.0	Α
Total Power Dissipation (Tc = 25 °C)	P <sub>T1</sub>	70	W
Total Power Dissipation (T <sub>A</sub> = 25 °C)	P <sub>T2</sub>	1.5	W
Channel Temperature	Tch	150	°C
Storage Temperature	T <sub>stg</sub>	–55 to +150	°C
Single Avalanche Current**	las	3.0	Α
Single Avalanche Energy**	Eas	5.4	mJ

- \* PW  $\leq$  10  $\mu$ s, Duty Cycle  $\leq$  1 %
- \*\* Starting T<sub>ch</sub> = 25 °C, R<sub>G</sub> = 25  $\Omega$ , V<sub>GS</sub> = 20 V  $\rightarrow$  0





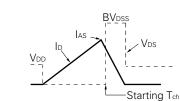


## **ELECTRICAL CHARACTERISTICS (TA = 25 °C)**

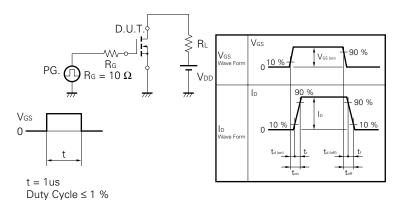
CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Drain to Source On-State Resistance	RDS(on)		5.6	7.5	Ω	Vgs = 10 V, ID = 2.0 A
Gate to Source Cutoff Voltage	V <sub>GS(off)</sub>	2.5		3.5	V	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA
Forward Transfer Admittance	y <sub>fs</sub>	8.0			S	V <sub>DS</sub> = 20 V, I <sub>D</sub> = 2.0 A
Drain Leakage Current	IDSS			100	μΑ	V <sub>DS</sub> = V <sub>DSS</sub> , V <sub>GS</sub> = 0
Gate to Source Leakage Current	Igss			±100	nA	V <sub>G</sub> S = ±30 V, V <sub>D</sub> S = 0
Input Capacitance	Ciss		485		pF	V <sub>DS</sub> = 10 V
Output Capacitance	Coss		75		pF	V <sub>G</sub> S = 0
Reverse Transfer Capacitance	Crss		10		pF	f = 1 MHz
Turn-On Delay Time	td(on)		12		ns	ID = 2.0 A
Rise Time	tr		5		ns	V <sub>GS</sub> = 10 V
Turn-Off Delay Time	td(off)		35		ns	V <sub>DD</sub> = 150 V
Fall Time	tf		8		ns	$R_G = 10 \Omega$
Total Gate Charge	Qg		17		nC	ID = 3.0 A
Gate to Source Charge	Qgs		3		nC	V <sub>DD</sub> = 450 V
Gate to Drain Charge	QgD		8		nC	V <sub>G</sub> S = 10 V
Body Diode Forward Voltage	V <sub>F(S-D)</sub>		1.0		٧	IF = 3.0 A, VGS = 0
Reverse Recovery Time	trr		670		ns	IF = 3.0 A, VGS = 0
Reverse Recovery Charge	Qrr		3.0		μC	di/dt = 50 A/μs

## Test Circuit 1 Avalanche Capability

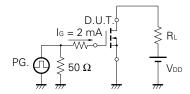
# $V_{GS} = 20 - 0 \text{ V}$ $V_{GS} = 20 - 0 \text{ V}$



## Test Circuit 2 Switching Time

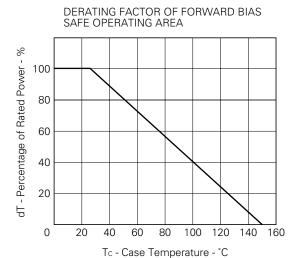


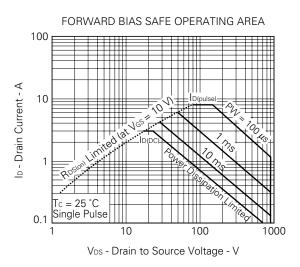
#### Test Circuit 3 Gate Charge

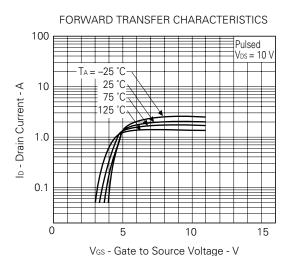


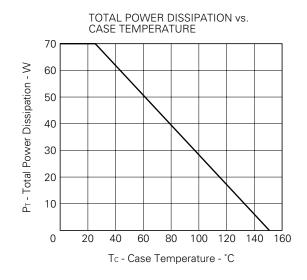
The application circuits and their parameters are for references only and are not intended for use in actual design-in's.

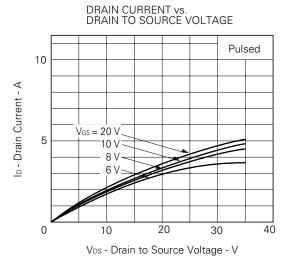
## TYPICAL CHARACTERISTICS (TA = 25 °C)



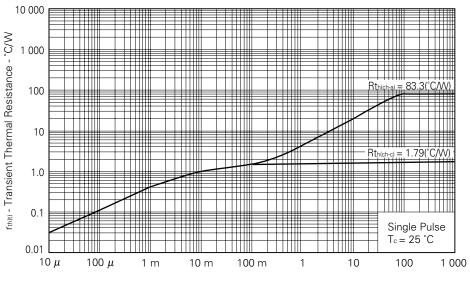






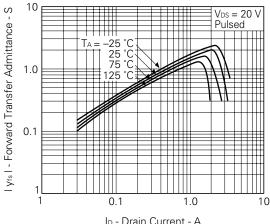


### TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

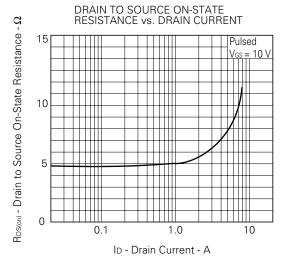


PW - Pulse Width - s

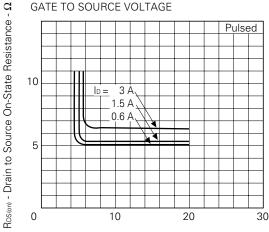
#### FORWARD TRANSFER ADMITTANCE vs. **DRAIN CURRENT**



ID - Drain Current - A

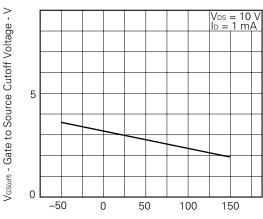


#### DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

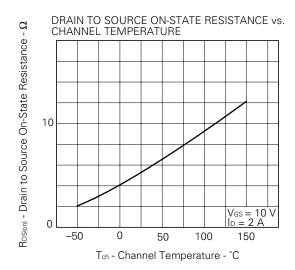


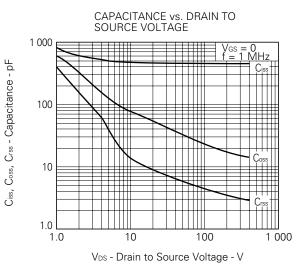
V<sub>GS</sub> - Gate to Source Voltage - V

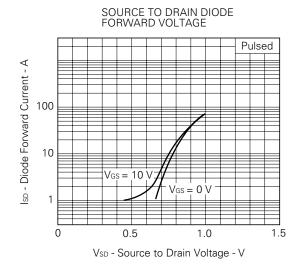
# GATE TO SOURCE CUTOFF VOLTAGE vs. CHANNEL TEMPERATURE

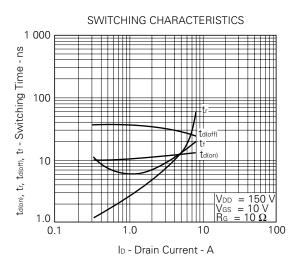


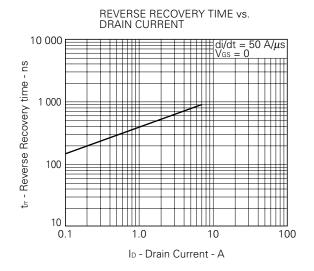
 $\mathsf{T}_\mathsf{ch}$  - Channel Temperature -  $^\circ\mathsf{C}$ 

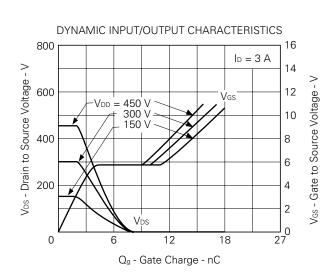




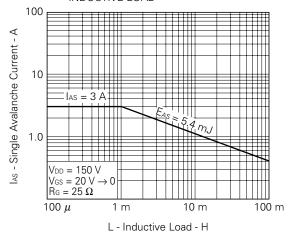




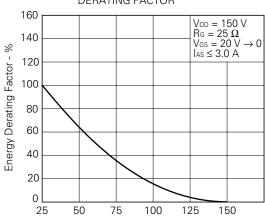




# SINGLE AVALANCHE CURRENT vs. INDUCTIVE LOAD



# SINGLE AVALANCHE ENERGY DERATING FACTOR



Starting  $T_{\text{ch}}$  - Starting Channel Temperature -  $^{\circ}\text{C}$ 



# REFERENCE

Document Name	Document No.
NEC semiconductor device reliability/quality control system.	TEI-1202
Quality grade on NEC semiconductor devices.	IEI-1209
Semiconductor device mounting technology manual.	IEI-1207
Semiconductor device package manual.	IEI-1213
Guide to quality assurance for semiconductor devices.	MEI-1202
Semiconductor selection guide.	MF-1134
Power MOS FET features and application switching power supply.	TEA-1034
Application circuits using Power MOS FET.	TEA-1035
Safe operating area of Power MOS FET.	TEA-1037



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